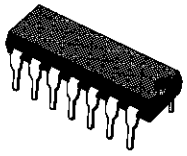
SGS-THOMSON MICROELECTRONICS

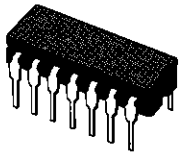
M54HC10
M74HC10

TRIPLE 3-INPUT NAND GATE

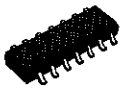
- HIGH SPEED
  t_{PD} = 6 ns (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 1 µA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 4 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS10



B1R
(Plastic Package)



F1R
(Ceramic Package)



M1R
(Micro Package)



C1R
(Chip Carrier)

ORDER CODES :

M54HC10F1R	M74HC10M1R
M74HC10B1R	M74HC10C1R

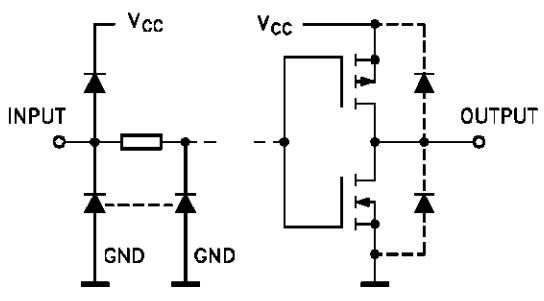
DESCRIPTION

The M54/74HC10 is a high speed CMOS TRIPLE 3-INPUT NAND GATE fabricated with silicon gate C^2MOS technology.

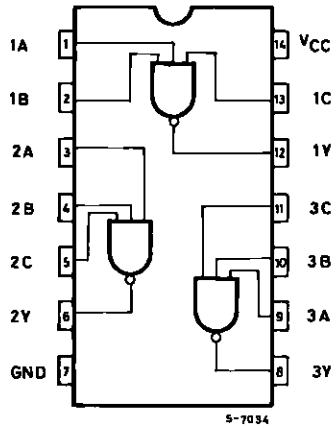
It has the same high speed performance of LSTTL combined with true CMOS low power consumption. The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

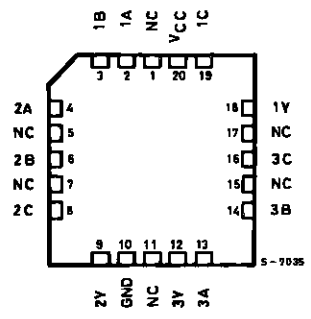
All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)



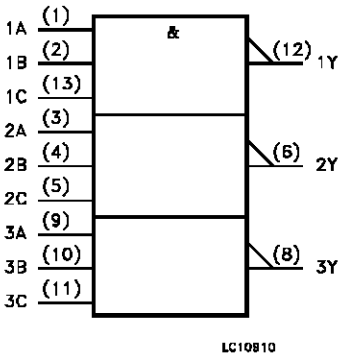


NC =
No Internal
Connection

TRUTH TABLE

A	B	C	Y
L	X	X	H
X	L	X	H
X	X	L	H
H	H	H	L

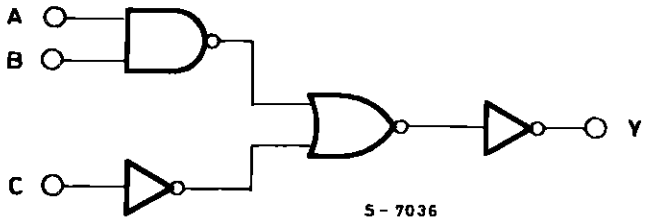
IEC LOGIC SYMBOL



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 9	1A to 3A	Data Inputs
2, 4, 10	1B to 3B	Data Inputs
13, 5, 11	1C to 3C	Data Inputs
12, 6, 8	1Y to 3Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

SCHEMATIC CIRCUIT (Per Gate)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	^oC ^oC
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

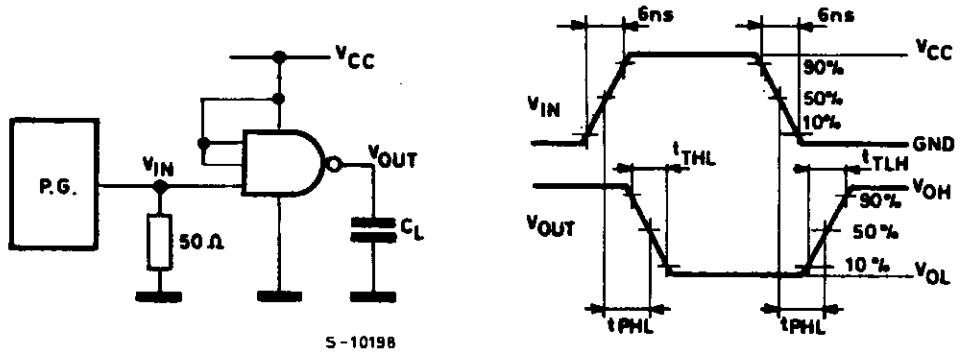
Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-5.2 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 4.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 5.2 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND				±0.1		±1		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				1		10		20	µA

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

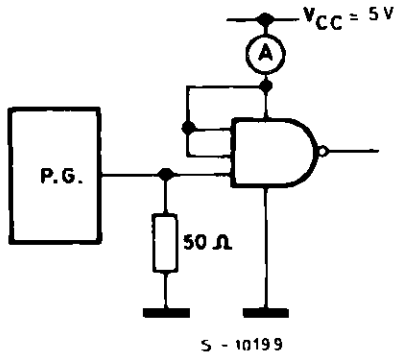
Symbol	Parameter	Test Conditions		Value							Unit
		V_{CC} (V)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0			27	75		95		110	ns
		4.5			9	15		19		22	
		6.0			8	13		16		19	
C_{IN}	Input Capacitance				5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance				23						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/3$ (per Gate)

SWITCHING CHARACTERISTICS TEST CIRCUIT



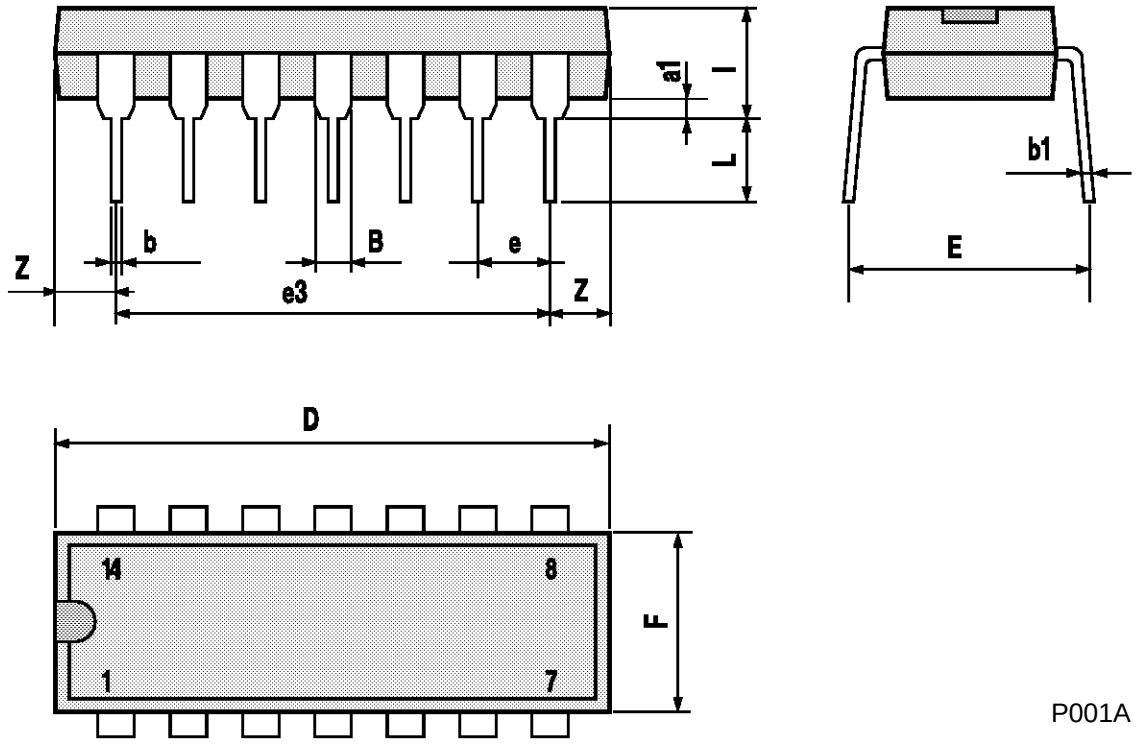
TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

Plastic DIP14 MECHANICAL DATA

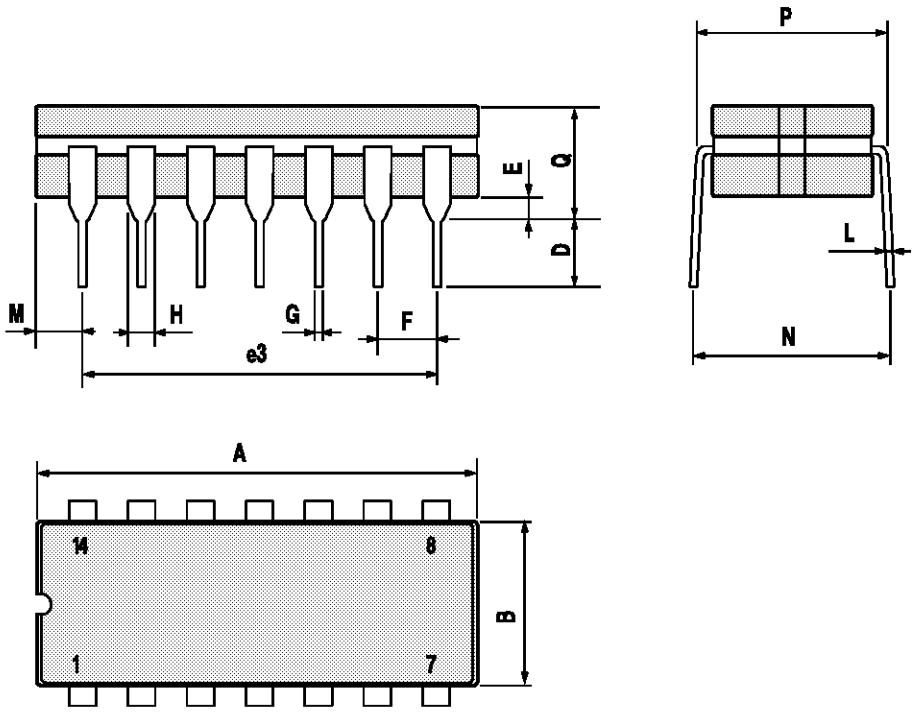
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

Ceramic DIP14/1 MECHANICAL DATA

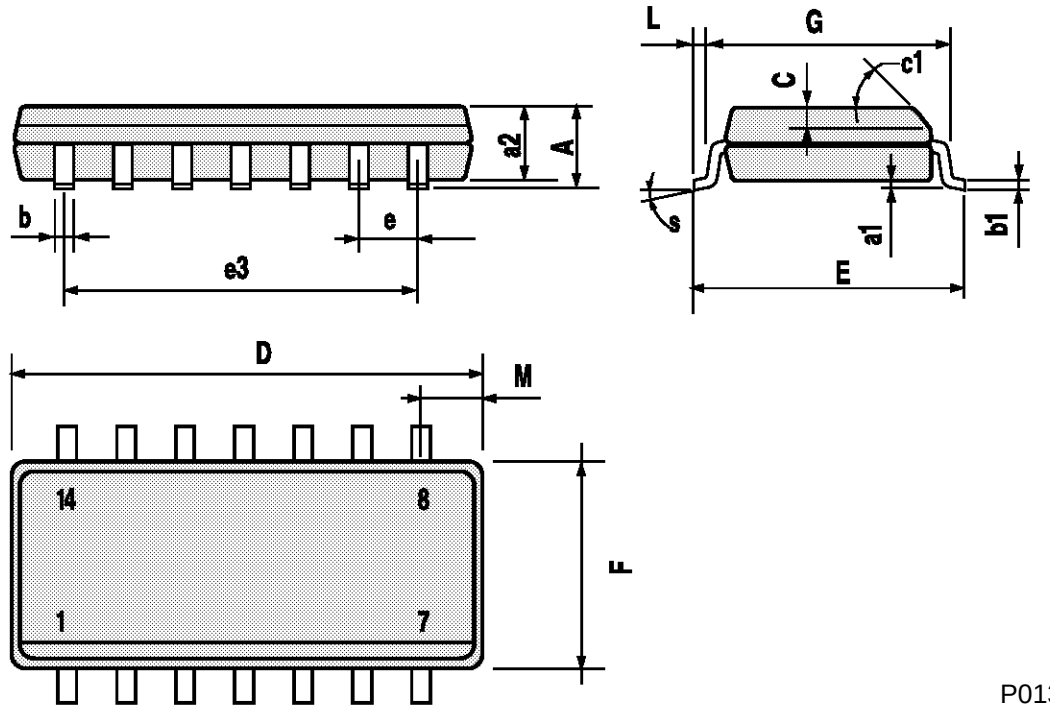
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7.0			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		15.24			0.600	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	1.52		2.54	0.060		0.100
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053C

SO14 MECHANICAL DATA

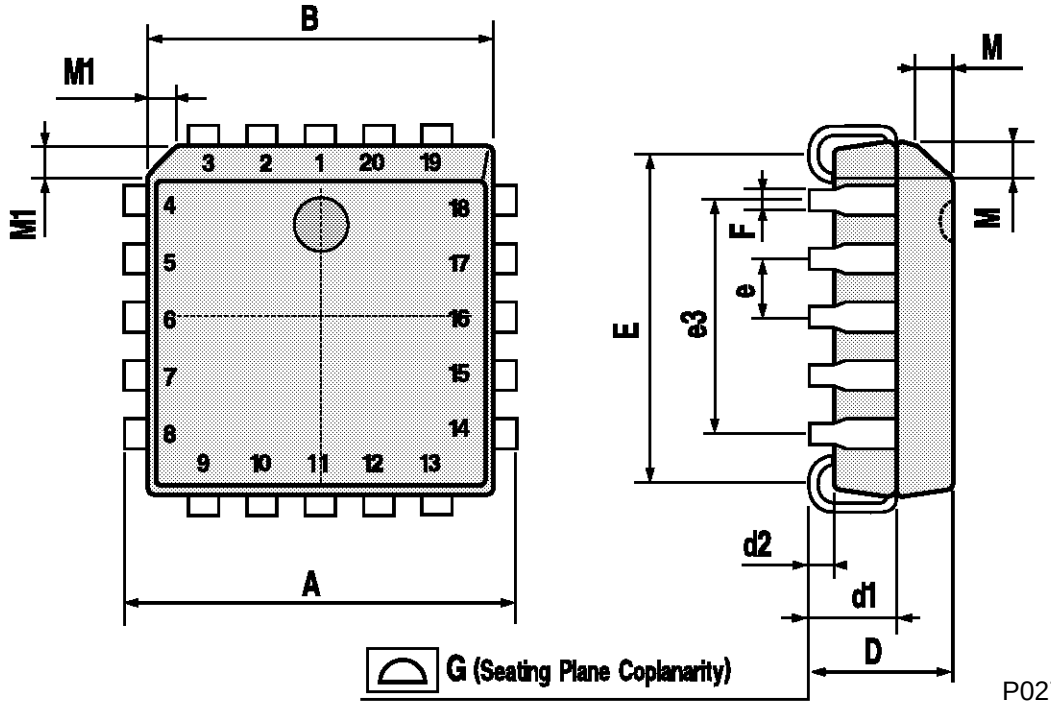
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



P013G

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



P027A

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